



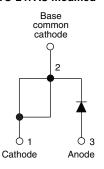
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Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 30 A



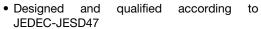
TO-247AC modified



PRODUCT SUMMARY						
Package	TO-247AC modified (2 pins)					
I _{F(AV)}	30 A					
V_R	1200 V					
V _F at I _F	4.1 V					
t _{rr} typ.	47 ns					
T _J max.	150 °C					
Diode variation	Single die					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}









ROHS
COMPLIANT
HALOGEN
FREE
Available

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA30PB120... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 30 A continuous current, the VS-HFA30PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tp portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA30PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V_{R}		1200	V		
Maximum continuous forward current	I _F	T _C = 100 °C	30			
Single pulse forward current	I _{FSM}		120	Α		
Maximum repetitive forward current	I _{FRM}		90			
Maximum naviar discination	Г	T _C = 25 °C	350	14/		
Maximum power dissipation	P _D	T _C = 100 °C	140	W		
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C		



VS-HFA30PB120PbF, VS-HFA30PB120-N3

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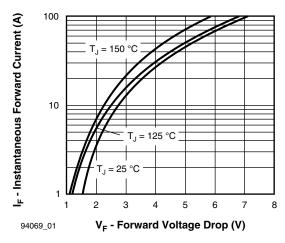
ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		1200	-	-	
Maximum forward voltage		I _F = 30 A		-	2.4	4.1	V
	V _{FM}	I _F = 60 A	See fig. 1	-	3.1	5.7	
		I _F = 30 A, T _J = 125 °C		-	2.3	4.0	
Maximum reverse		V _R = V _R rated	Cooffe O	-	1.3	40	
leakage current	I_{RM} I_{RM} See fig. 2		See lig. 2	-	1100	4000	μΑ
Junction capacitance	C _T	V _R = 200 V	See fig. 3	-	50	75	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body		-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$) A/μs, V _R = 30 V	-	47	-	
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C		-	110	170	ns
occ lig. 5, 10	t _{rr2}	T _J = 125 °C	I _F = 30 A	-	170	260	
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	10	15	А
See fig. 6	I _{RRM2}	T _J = 125 °C		-	16	24	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	dl _F /dt = 200 A/μs	-	650	980	nC
See fig. 7	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	1540	2310	IIC
Peak rate of fall of recovery current during t_b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	270	-	A/µs
	dI _{(rec)M} /dt2	T _J = 125 °C		-	240	-	Ανμδ

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	0.36		
Thermal resistance, junction to ambient	R _{thJA}	R _{thJA} Typical socket mount		-	80	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased		0.50	-		
Weight			-	5.61	-	g	
vveigni			-	0.198	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-247AC modified (JEDEC)	HFA30PB120				



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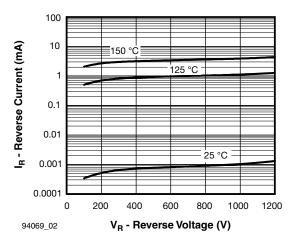


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

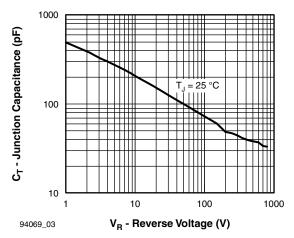


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

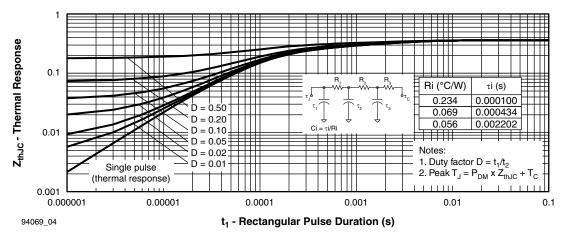


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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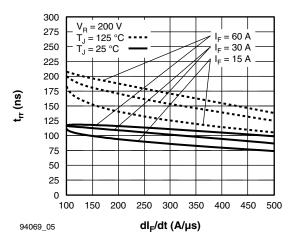


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

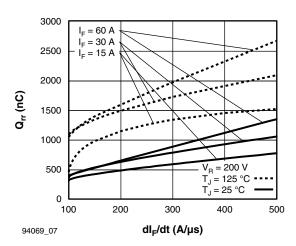


Fig. 7 - Typical Stored Charge vs. dI_F/dt (Per Leg)

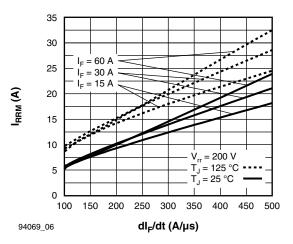


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

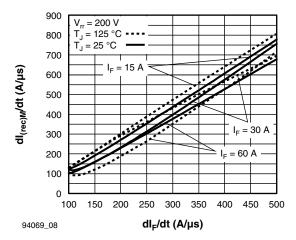


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt(Per Leg)

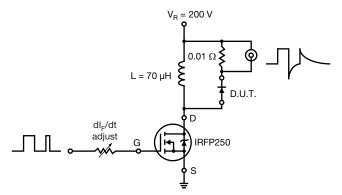
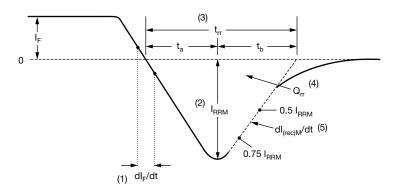


Fig. 9 - Reverse Recovery Parameter Test Circuit

VS-HFA30PB120PbF, VS-HFA30PB120-N3

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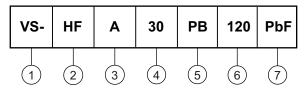


- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}
 - $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (5) dI_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- 2 HEXFRED® family
- Electron irradiated
- Current rating (30 = 30 A)
- 5 PB = TO-247AC modified
- Voltage rating: (120 = 1200 V)
- 7 Environmental digit:

PbF = Lead (Pb)-free and RoHS-compliant

-N3 = Halogen-free, RoHS-compliant and totally lead (Pb)-free

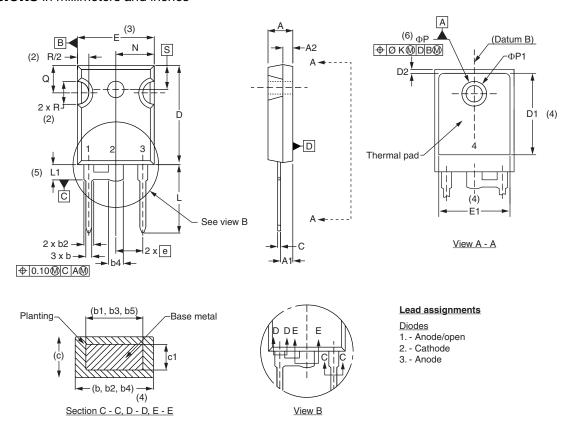
ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA30PB120PbF	25	500	Antistatic plastic tube				
VS-HFA30PB120-N3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS						
Dimensions		www.vishay.com/doc?95253				
Dant an adding a information	TO-247AC modified PbF	www.vishay.com/doc?95255				
Part marking information	TO-247AC modified -N3	www.vishay.com/doc?95442				
SPICE model		www.vishay.com/doc?95358				



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DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INCHES		NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.37	0.065	0.094	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.86	0.015	0.034	
c1	0.38	0.76	0.015	0.030	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.72	-	0.540	1	
е	5.46 BSC		0.215	BSC	
ΦК	2.	54	0.010		
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
N	7.62 BSC		0	.3	
ΦР	3.56	3.66	0.14	0.144	
ФР1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	1.78	0.216	
S	5.51	BSC	0.217	BSC	

Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) ΦP to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c



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